

TO-277 Schottky Barrier Rectifier Diode 肖特基势垒整流二极管

■ **Features 特点**

Low forward voltage drop 低正向压降
High current capability 高电流能力
Surface mount device 表面贴装器件
Case 封装:TO-277



■ **Maximum Rating 最大额定值**

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	SB540L	SB545L	SB550L	SB560L	SB580L	SB5100L	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	40	45	50	60	80	100	V
DC Reverse Voltage 直流反向电压	V_R	40	45	50	60	80	100	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	28	32	35	42	56	70	V
Forward Rectified Current 正向整流电流	I_F	5						A
Peak Surge Current 峰值浪涌电流	I_{FSM}	120						A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	60						$^{\circ}\text{C}/\text{W}$
Junction Temperature 结温	T_J	150						$^{\circ}\text{C}$
Storage Temperature 储藏温度	T_{stg}	-55to+150 $^{\circ}\text{C}$						

■ **Electrical Characteristics 电特性**

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	SB540L-SB550L	SB560L	SB580L-SB5100L	Unit 单位	Condition 条件
Forward Voltage 正向电压	V_F	0.35	0.40	0.45	V	$I_F=2\text{A}$
		0.48	0.55	0.70		$I_F=5\text{A}$
Reverse Current 反向电流	$I_R(25^{\circ}\text{C})$	0.5		0.2	mA	$V_R=V_{RRM}$
	$I_R(125^{\circ}\text{C})$	50		20		

■ Typical Characteristic Curve 典型特性曲线

FIG. 1- DERATING CURVE OUTPUT RECTIFIED CURRENT

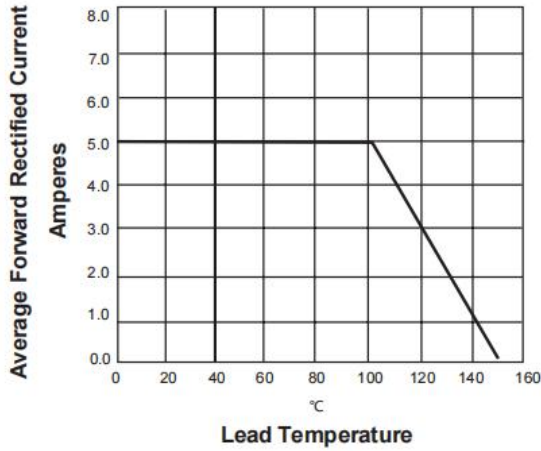


FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT PER LEG

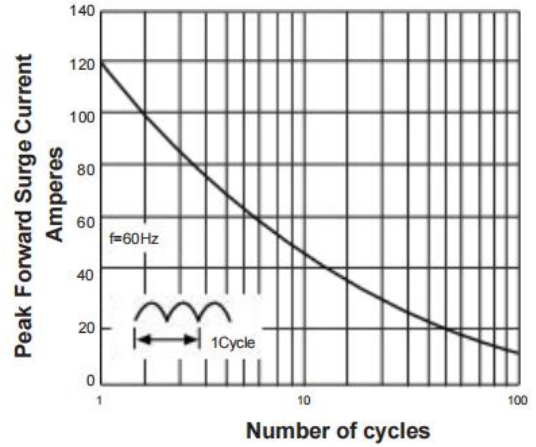


FIG. 3-TYPICAL FORWARD VOLTAGE CHARACTERISTICS

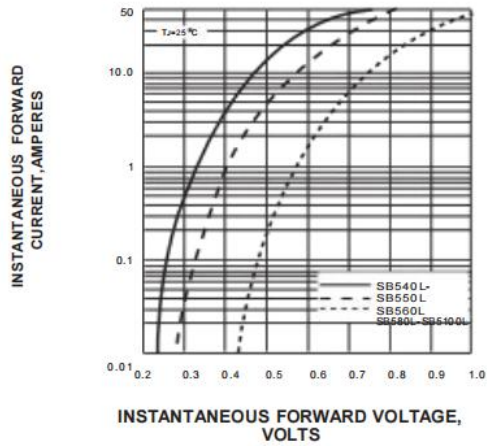
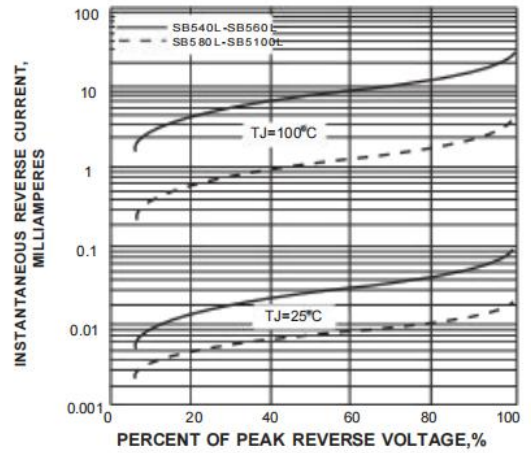
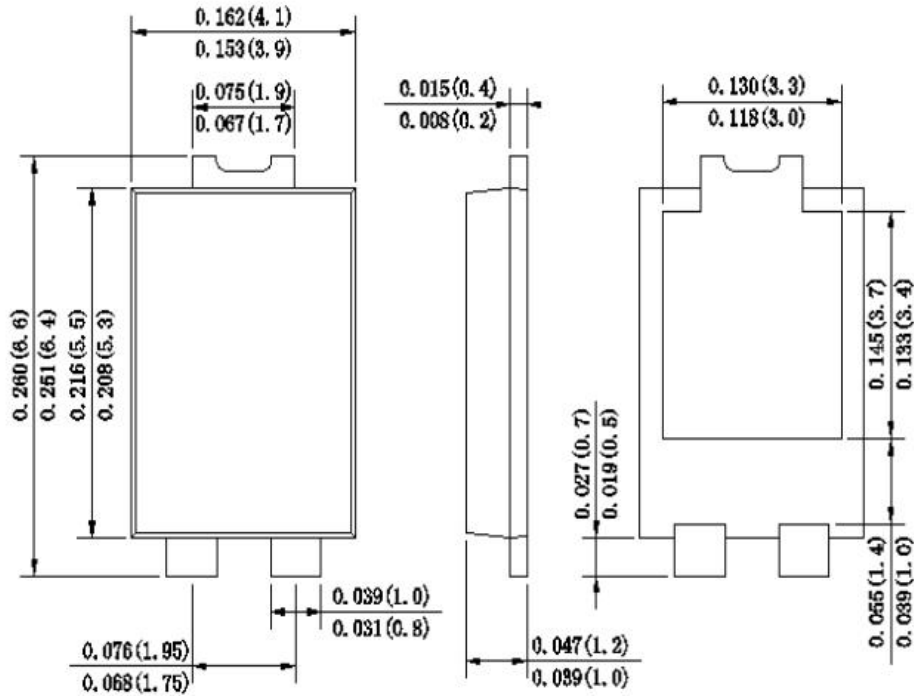


FIG. 4-TYPICAL REVERSE LEAKAGE CHARACTERISTICS



■ Dimension 外形封装尺寸



Dimensions in inches and (millimeters)